

# **2PD601ART**

# 50 V, 100 mA NPN general-purpose transistor Rev. 01 — 15 March 2007

**Product data sheet** 

### **Product profile**

### 1.1 General description

NPN general-purpose transistor in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package.

PNP complement: 2PB709ART.

#### 1.2 Features

- General-purpose transistor
- Small SMD plastic package

### 1.3 Applications

■ General-purpose switching and amplification

### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{CEO}$	collector-emitter voltage	open base	-	-	50	V
I <sub>C</sub>	collector current		-	-	100	mA
h <sub>FE</sub>	DC current gain	$V_{CE} = 10 \text{ V};$ $I_C = 2 \text{ mA}$	210	-	340	

## 2. Pinning information

Table 2. **Pinning** 

Pin	Description	Simplified outline	Symbol
1	base		
2	emitter	3	3
3	collector	1 2	1 —
			sym021



### 50 V, 100 mA NPN general-purpose transistor

# 3. Ordering information

Table 3. Ordering information

Type number Package			
	Name	Description	Version
2PD601ART	-	plastic surface-mounted package; 3 leads	SOT23

### 4. Marking

Table 4. Marking codes

Type number	Marking code <sup>[1]</sup>
2PD601ART	C3*

<sup>[1] \* = -:</sup> made in Hong Kong

# 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CBO}$	collector-base voltage	open emitter	-	60	V
$V_{CEO}$	collector-emitter voltage	open base	-	50	V
$V_{EBO}$	emitter-base voltage	open collector	-	6	V
I <sub>C</sub>	collector current		-	100	mA
I <sub>CM</sub>	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	200	mA
I <sub>BM</sub>	peak base current	single pulse; $t_p \le 1 \text{ ms}$	-	100	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25  ^{\circ}C$	<u>[1]</u> _	250	mW
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-65	+150	°C
$T_{stg}$	storage temperature		-65	+150	°C

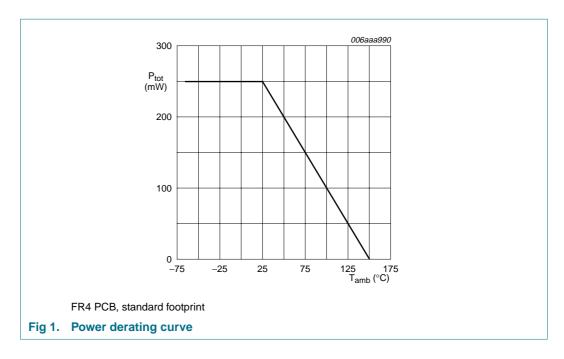
<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

<sup>\* =</sup> p: made in Hong Kong

<sup>\* =</sup> t: made in Malaysia

<sup>\* =</sup> W: made in China

### 50 V, 100 mA NPN general-purpose transistor



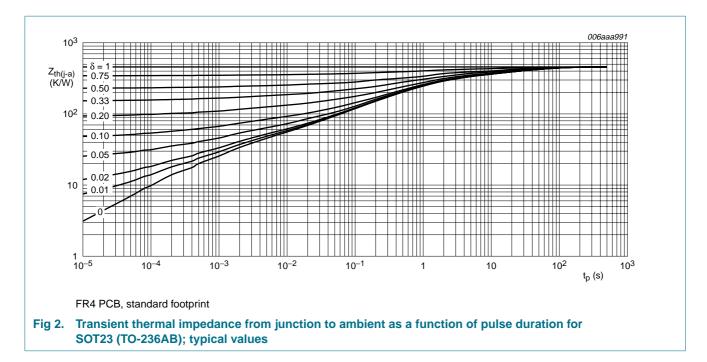
### 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u> -	-	500	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point		-	-	140	K/W

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

### 50 V, 100 mA NPN general-purpose transistor



### 7. Characteristics

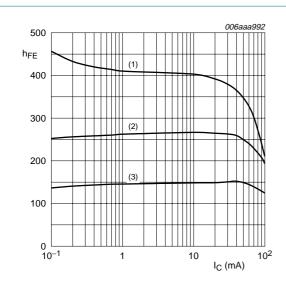
Table 7. Characteristics

 $T_{amb} = 25 \,^{\circ}C$  unless otherwise specified.

	•					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$I_{CBO}$	collector-base cut-off	$V_{CB} = 60 \text{ V}; I_E = 0 \text{ A}$	-	-	10	nA
	current	$V_{CB} = 60 \text{ V}; I_E = 0 \text{ A};$ $T_j = 150 \text{ °C}$	-	-	5	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}$	-	-	10	nA
h <sub>FE</sub>	DC current gain	$V_{CE} = 2 V;$ $I_{C} = 100 \text{ mA}$	90	-	-	
		$V_{CE} = 10 \text{ V};$ $I_{C} = 2 \text{ mA}$	210	-	340	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = 100 \text{ mA};$ $I_B = 10 \text{ mA}$	[1] -	-	250	mV
f <sub>T</sub>	transition frequency	$V_{CE} = 10 \text{ V};$ $I_{C} = 2 \text{ mA};$ $f = 100 \text{ MHz}$	100	-	-	MHz
C <sub>c</sub>	collector capacitance	$V_{CB} = 10 \text{ V};$ $I_E = i_e = 0 \text{ A};$ $f = 1 \text{ MHz}$	-	-	3	pF

<sup>[1]</sup> Pulse test:  $t_p \le 300 \ \mu s; \ \delta \le 0.02$ .

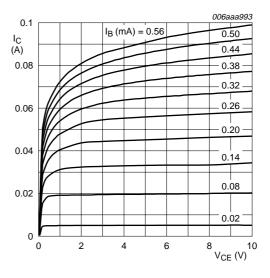
### 50 V, 100 mA NPN general-purpose transistor



$$V_{CE} = 10 \text{ V}$$

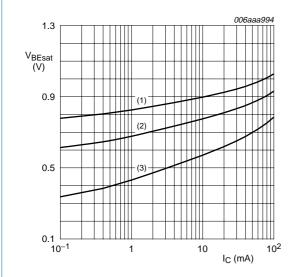
- (1)  $T_{amb} = 150 \, ^{\circ}C$
- (2)  $T_{amb} = 25 \,^{\circ}C$
- (3)  $T_{amb} = -55 \, ^{\circ}C$

Fig 3. DC current gain as a function of collector current; typical values



T<sub>amb</sub> = 25 °C

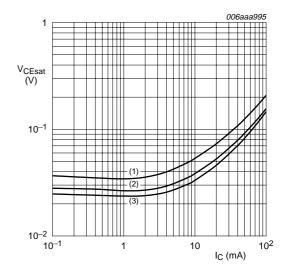
Fig 4. Collector current as a function of collector-emitter voltage; typical values





- (1)  $T_{amb} = -55 \, ^{\circ}C$
- (2) T<sub>amb</sub> = 25 °C
- (3)  $T_{amb} = 150 \, ^{\circ}C$

Fig 5. Base-emitter saturation voltage as a function of collector current; typical values



 $I_{\rm C}/I_{\rm B} = 10$ 

- (1)  $T_{amb} = 150 \, ^{\circ}C$
- (2)  $T_{amb} = 25 \, ^{\circ}C$

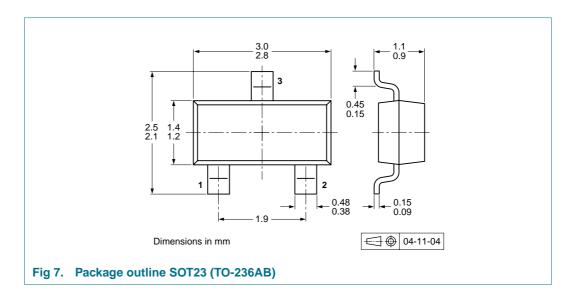
Rev. 01 — 15 March 2007

(3)  $T_{amb} = -55 \, ^{\circ}C$ 

Fig 6. Collector-emitter saturation voltage as a function of collector current; typical values

50 V, 100 mA NPN general-purpose transistor

# 8. Package outline



# 9. Packing information

Table 8. Packing methods

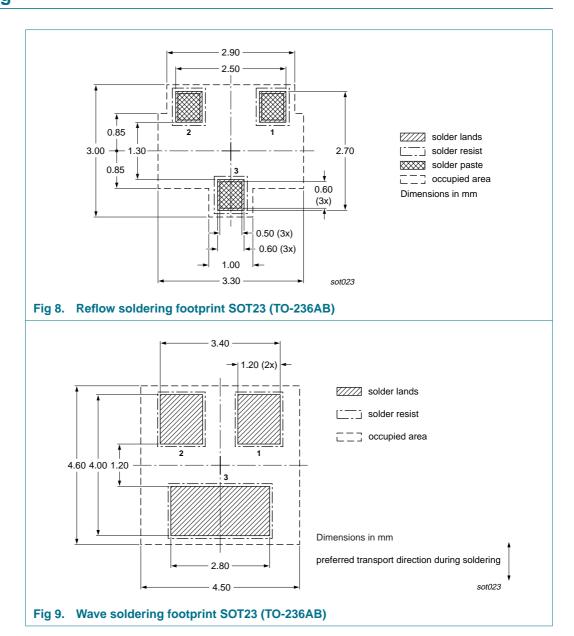
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description Packing quantit		quantity
			3000	10000
2PD601ART	SOT23	4 mm pitch, 8 mm tape and reel	-215	-235

[1] For further information and the availability of packing methods, see Section 13.

### 50 V, 100 mA NPN general-purpose transistor

# 10. Soldering



50 V, 100 mA NPN general-purpose transistor

# 11. Revision history

### Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
2PD601ART_1	20070315	Product data sheet	-	-

### 50 V, 100 mA NPN general-purpose transistor

### 12. Legal information

#### 12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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# **2PD601ART**

### 50 V, 100 mA NPN general-purpose transistor

### 14. Contents

1	Product profile
1.1	General description
1.2	Features
1.3	Applications 1
1.4	Quick reference data
2	Pinning information 1
3	Ordering information
4	Marking 2
5	Limiting values
6	Thermal characteristics 3
7	Characteristics4
8	Package outline 6
9	Packing information6
10	Soldering 7
11	Revision history8
12	Legal information9
12.1	Data sheet status
12.2	Definitions
12.3	Disclaimers
12.4	Trademarks9
13	Contact information 9
14	Contents

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